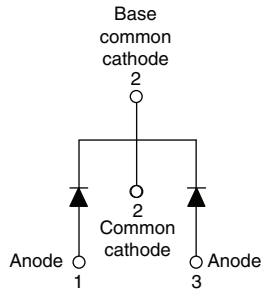


HEXFRED®

Ultrafast Soft Recovery Diode, 2 x 15 A



TO-220AB



PRODUCT SUMMARY	
Package	TO-220AB
$I_{F(AV)}$	2 x 15 A
V_R	600 V
V_F at I_F	1.7 V
t_{rr} typ.	19 ns
T_J max.	150 °C
Diode variation	Common cathode

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE


RoHS
 COMPLIANT
 HALOGEN
FREE

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA30TA60CHN3 is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A per leg continuous current, the VS-HFA30TA60CHN3 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to “snap-off” during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30TA60CHN3 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_R		600	V
Maximum continuous forward current	I_F	$T_C = 100\text{ °C}$	per leg 15	A
			per device 30	
Single pulse forward current	I_{FSM}		150	
Maximum repetitive forward current	I_{FRM}		60	
Maximum power dissipation	P_D	$T_C = 25\text{ °C}$	74	W
		$T_C = 100\text{ °C}$	29	
Operating junction and storage temperature range	T_J, T_{Stg}		-55 to +150	°C



ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	$I_R = 100\text{ }\mu\text{A}$	600	-	-	V
Maximum forward voltage	V_{FM}	$I_F = 15\text{ A}$	-	1.3	1.7	
		$I_F = 30\text{ A}$	-	1.5	2.0	
		$I_F = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	1.2	1.6	
Maximum reverse leakage current	I_{RM}	$V_R = V_R$ rated	-	1.0	10	μA
		$T_J = 125\text{ }^\circ\text{C}, V_R = 0.8 \times V_R$ rated	-	400	1000	
Junction capacitance	C_T	$V_R = 200\text{ V}$	-	25	50	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8	-	nH

DYNAMIC RECOVERY CHARACTERISTICS PER LEG ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5 and 10	t_{rr}	$I_F = 1.0\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, V_R = 30\text{ V}$	-	19	-	ns
	t_{rr1}	$T_J = 25\text{ }^\circ\text{C}$	-	42	60	
	t_{rr2}	$T_J = 125\text{ }^\circ\text{C}$	-	70	120	
Peak recovery current See fig. 6	I_{RRM1}	$T_J = 25\text{ }^\circ\text{C}$	-	4.0	6.0	A
	I_{RRM2}	$T_J = 125\text{ }^\circ\text{C}$	-	6.5	10	
Reverse recovery charge See fig. 7	Q_{rr1}	$T_J = 25\text{ }^\circ\text{C}$	-	80	180	nC
	Q_{rr2}	$T_J = 125\text{ }^\circ\text{C}$	-	220	600	
Peak rate of fall of recovery current during t_b See fig. 8	$di_{(rec)M}/dt1$	$T_J = 25\text{ }^\circ\text{C}$	-	250	-	$\text{A}/\mu\text{s}$
	$di_{(rec)M}/dt2$	$T_J = 125\text{ }^\circ\text{C}$	-	160	-	

THERMAL - MECHANICAL SPECIFICATIONS PER LEG						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T_{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	$^\circ\text{C}$
Junction to case, single leg conducting	R_{thJC}				1.7	K/W
Junction to case, both legs conducting			-	-	0.85	
Thermal resistance, junction to ambient	R_{thJA}	Typical socket mount	-	-	40	
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-	
Weight			-	6.0	-	g
			-	0.21	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	$\text{kgf} \cdot \text{cm}$ ($\text{lb} \cdot \text{in}$)
Marking device		Case style TO-220AB	HFA30TA60CH			

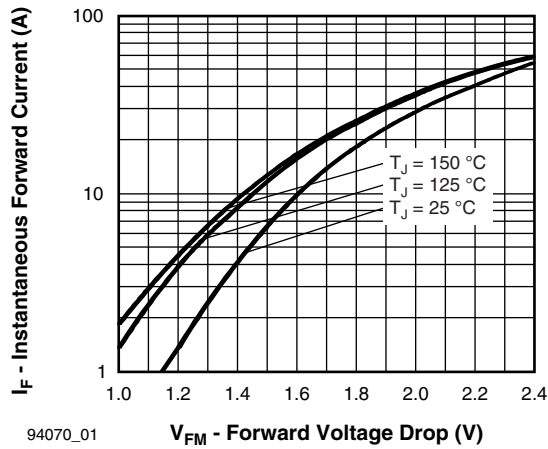


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

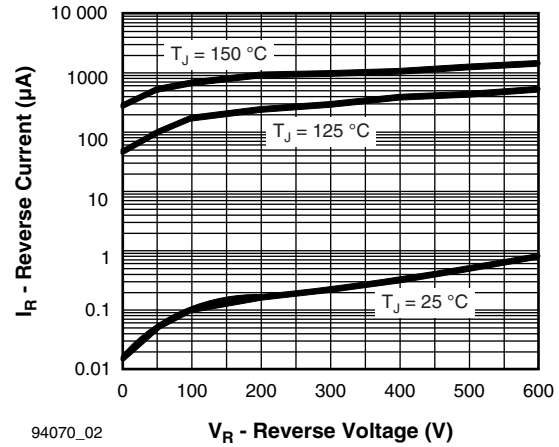


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

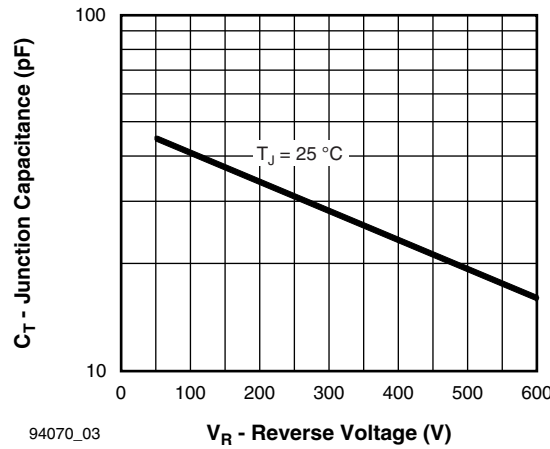


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

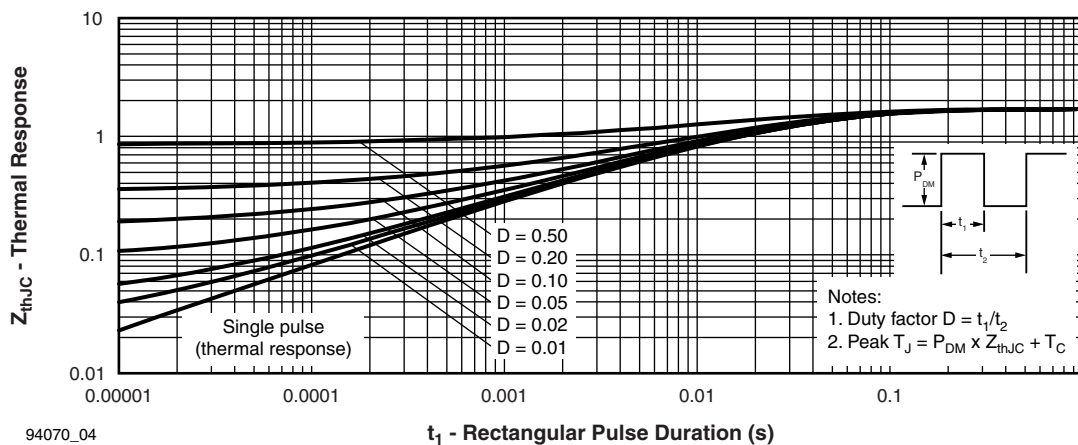
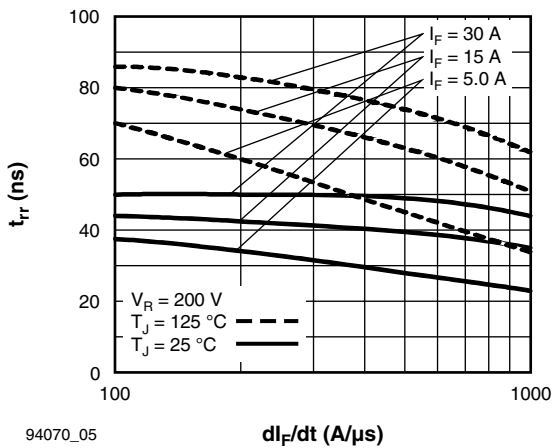
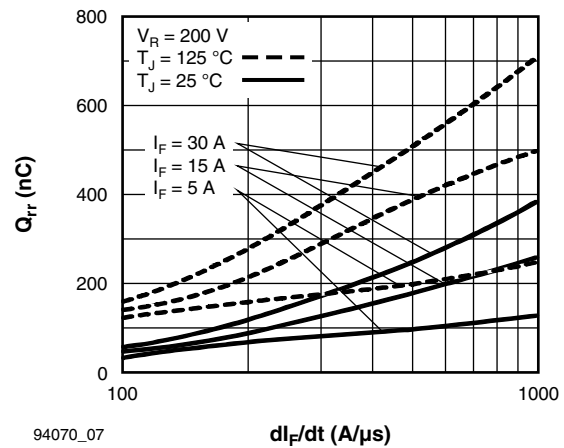


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)



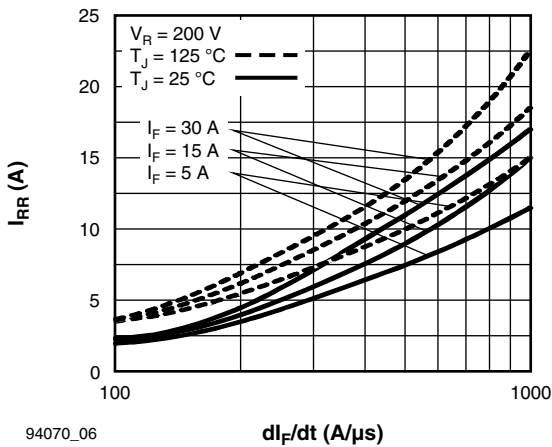
94070_05

Fig. 5 - Typical Reverse Recovery Time vs. di_F/dt (Per Leg)



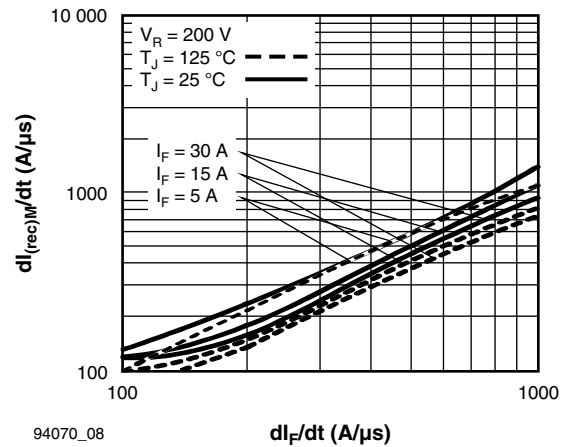
94070_07

Fig. 7 - Typical Stored Charge vs. di_F/dt (Per Leg)



94070_06

Fig. 6 - Typical Recovery Current vs. di_F/dt (Per Leg)



94070_08

Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_F/dt (Per Leg)

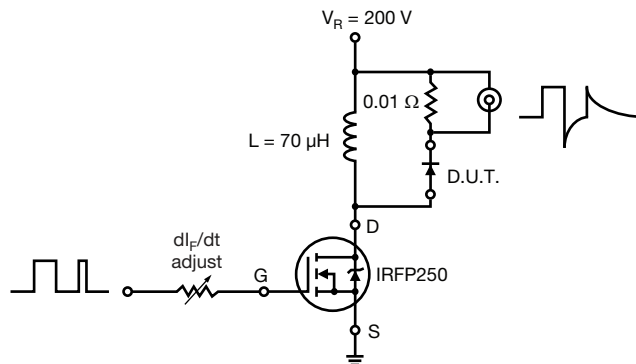
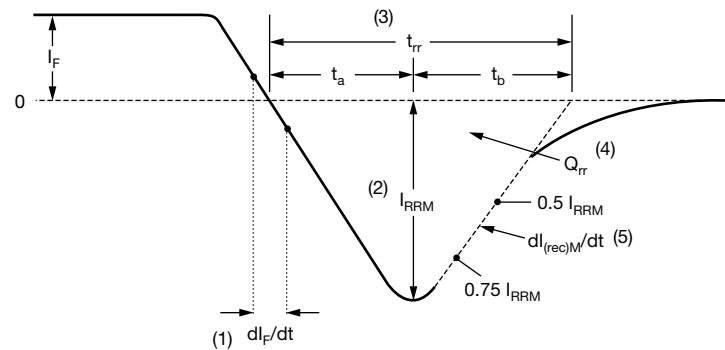


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt - rate of change of current through zero crossing
- (2) I_{RRM} - peak reverse recovery current
- (3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}
- $$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$
- (5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code	VS-	HF	A	30	TA	60	C	H	N3
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Vishay Semiconductors product
- 2** - HEXFRED® family
- 3** - Electron irradiated
- 4** - Current rating (30 = 30 A)
- 5** - Package:
TA = TO-220AB
- 6** - Voltage rating (60 = 600 V)
- 7** - Circuit configuration:
C = Common cathode
- 8** - H = AEC-Q101 qualified
- 9** - Environmental digit:
N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-HFA30TA60CHN3	25	500	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95222
Part marking information	TO-220AB-N3 www.vishay.com/doc?95028



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.